MICROWAVE POWER GaAs FET TIM7785-6UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET ·HIGH POWER
- P1dB= 38.5dBm at 7.7GHz to 8.5GHz

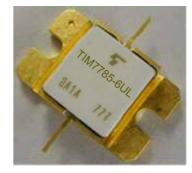
·HIGH GAIN

G1dB= 8.5dB at 7.7GHz to 8.5GHz

·LOW INTERMODULATION DISTORTION

IM3(MIN.) = -44dBc at Pout= 27.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.		
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 1.3A f= 7.7 to 8.5GHz Two-Tone Test Po= 27.5dBm, ∆f= 5MHz (Single Carrier Level)	dBm	37.5	38.5	_		
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.5	8.5			
Drain Current	IDS1		А		1.6	1.9		
Gain Flatness	ΔG		dB	_		±0.6		
Power Added Efficiency	ηadd		%		38			
3rd Order Intermodulation Distortion	IM3		dBc	-44	-47			
Drain Current	IDS2		А		1.3	1.5		
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_	_	80		

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 150 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.0A	s	_	1.24	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 20mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А		3.6	
Gate-Source Breakdown Voltage	VGSO	IGS= -70μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		3.8	4.6

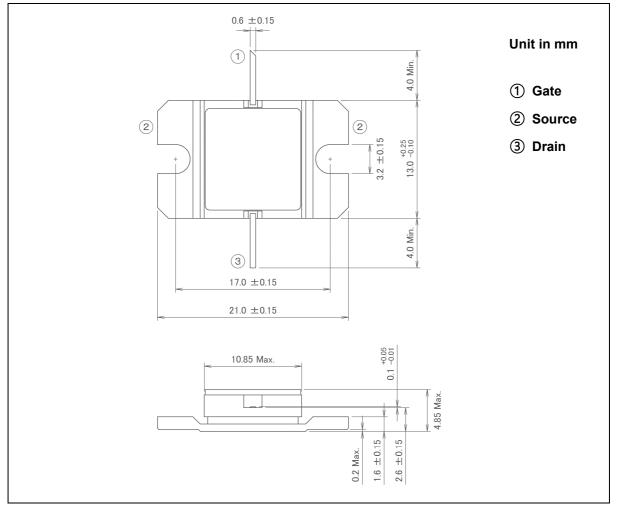
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

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CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	5.0
Total Power Dissipation (Tc= 25°C)	PT	W	32.6
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11D1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

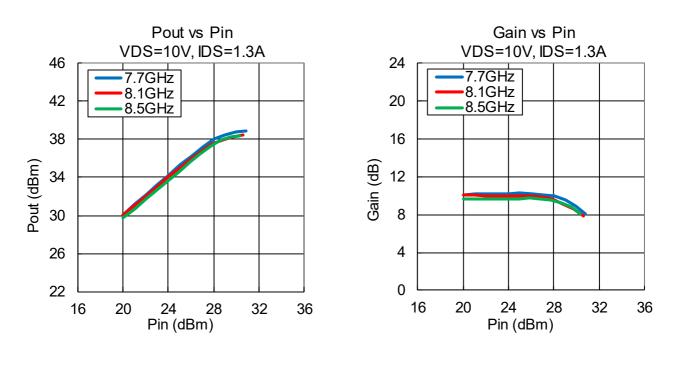
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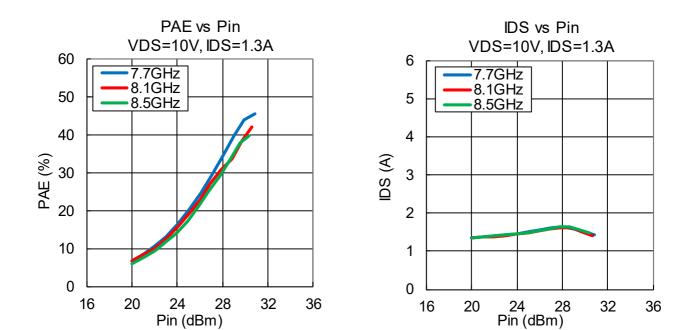
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TYPICAL RF PERFORMANCE

·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 1.3 A, f= 7.7, 8.1, 8.5 GHz, Ta= +25 °C



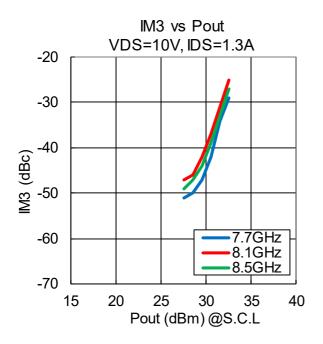


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·IM3 vs. Pout

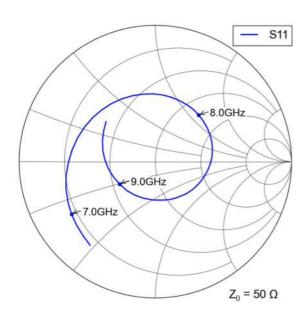
VDS= 10 V, IDSset= 1.3 A, f= 7.7, 8.1, 8.5 GHz, Δ f= 5 MHz , Ta= +25 $^\circ$ C

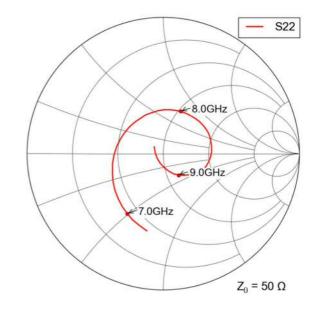


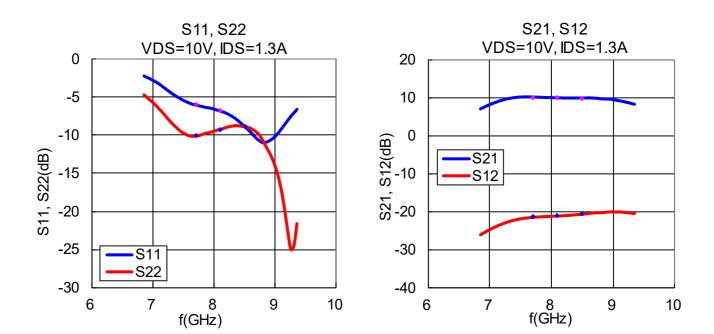
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·S-Parameters

VDS= 10 V, IDSset= 1.3 A, f= 6.85 to 9.35 GHz, Ta= +25 ℃







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